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# Enhanced visible light absorption performance of SnS<sub>2</sub> and SnSe<sub>2</sub> via surface charge transfer doping†

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The layered two-dimensional (2D) SnS<sub>2</sub> and SnSe<sub>2</sub> have received intensive attention due to their sizable band gaps and potential properties. However, it has been shown that the visible light absorption of SnS<sub>2</sub> and SnSe<sub>2</sub> are restricted as photocatalysts and light-harvesting material absorbers for water splitting and high-performance optoelectronic devices. Herein, to enhance the visible light absorption performance of SnS<sub>2</sub> and SnSe<sub>2</sub>, we performed a systematic investigation on tuning the electronic and optical properties of monolayers SnS<sub>2</sub> and SnSe<sub>2</sub> via surface charge transfer doping (SCTD) with the adsorption of molybdenum trioxide (MoO<sub>3</sub>) and potassium (K) as surface dopants based on density functional theory. Our calculations reveal that MoO<sub>3</sub> molecules and K atoms can draw/donate electrons from/to SnS<sub>2</sub> and SnSe<sub>2</sub> as acceptors and donors, respectively. The adsorption of MoO<sub>3</sub> molecules introduces a new flat impurity state in the gap of the monolayers SnS<sub>2</sub>/SnSe<sub>2</sub>, and the Fermi level moves correspondingly to the top of valence band, resulting in a p-type doping of the monolayer SnS<sub>2</sub>/SnSe<sub>2</sub>. With the adsorption of K atoms, the electrons can transfer from K atoms to the monolayer of SnS<sub>2</sub> and SnSe<sub>2</sub>, making K an effective electron-donating dopant. Meanwhile, the bandgaps of monolayers SnS<sub>2</sub> and SnSe<sub>2</sub> decrease after the MoO<sub>3</sub> and K doping, which leads to the appearance of appreciable new absorption peaks at around ~650/480 and ~600/680 nm, respectively, and yielding an enhanced visible light absorption of SnS<sub>2</sub> and SnSe<sub>2</sub>. Our results unveil that SCTD is an effective way to improve the photocatalytic and light-harvesting performance of SnS<sub>2</sub> and SnSe<sub>2</sub>, broadening their applications in splitting water and degrading environmental pollutants under sunlight irradiation.

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## Introduction

Since Fujishima and Honda discovered the photocatalytic splitting of water on TiO<sub>2</sub> electrodes in 1972,<sup>1</sup> the TiO<sub>2</sub> nanostructures have attracted much research attention as photocatalysts due to its promising applications in the efficient conversion of sunlight to environmentally friendly renewable energy and the treatment of environmental pollution.<sup>2,3</sup> However, the photoreaction efficiency of TiO<sub>2</sub> is severely limited by its large intrinsic band gap (*e.g.*, for the anatase phase, 3.20 eV), which makes it impossible to utilize the visible light of solar spectrum.<sup>4</sup>

As one type of the two-dimensional (2D) layered chalcogenide materials (LCMs), tin dichalcogenides SnX<sub>2</sub> (X = S and Se) have potential performance such as low toxicity, easy availability and high chemical and thermal stability with

a hexagonal crystal structure of the type CdI<sub>2</sub>,<sup>5,6</sup> making their wide range of applications in gas sensing,<sup>7,8</sup> anode materials,<sup>9,10</sup> photochemical reactions,<sup>11–19</sup> and optoelectronic devices.<sup>20–22</sup> Of particular note is that, due to their high specific surface area, ultrathin SnS<sub>2</sub> and SnSe<sub>2</sub> are widely investigated as photocatalysts and light-harvesting material absorbers for photochemical reactions<sup>11–26</sup> and optoelectronic devices,<sup>27–29</sup> respectively. For instance, freestanding SnS<sub>2</sub> single-layers with three atom thickness were first synthesized through a convenient and scalable liquid exfoliation strategy, offering an excellent platform to achieve efficient visible-light water splitting, which can approach a higher visible-light conversion efficiency (38.7%) than that of bulk phase (2.33%).<sup>11</sup> Also, it is reported that ultrathin SnS<sub>2</sub> nanosheets are utilized as solar-driven photocatalyst, but there is quite challenging to explore a material with suitable band alignment using SnS<sub>2</sub> nanomaterials for photocatalytic hydrogen generation.<sup>14</sup> Nevertheless, the theoretical perspective showed that the optical band gap lied within the range of visible light,<sup>15</sup> implying a significant fraction of solar light can be harvested by single-layer SnS<sub>2</sub>, but the overall water splitting cannot spontaneously take place on the SnS<sub>2</sub> nanosheets because the conduction band minimum (CBM) is insufficient to drive the hydrogen evolution. Yu *et al.* also discovered SnS<sub>2</sub> nanosheets exhibit the highest

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photocatalytic hydrogen generation ability, which may be attributed to narrower optical band gap and unique 2D morphology.<sup>16</sup> In addition, Mukhokosi *et al.*<sup>28</sup> have observed that the band gap of SnSe<sub>2</sub> depends on thin film thickness, that is ~2.04 eV for 50 nm thick film similar to that of monolayers, whereas it is approximately 1.2 eV for the 1200 nm thick film similar to that of bulk phase. And the IR photodetection response of SnSe<sub>2</sub> demonstrates a sensitivity of ~3% for a 1000 nm thick film (bulk phase), but the sensitivity is 90.4% for 140 nm thick film (monolayers) at 100 mW cm<sup>-2</sup>, suggesting the SnSe<sub>2</sub> thin film can be explored as an excellent material for photodetection. Overall, all these results show that 2D layered SnS<sub>2</sub> and SnSe<sub>2</sub> are restricted as photocatalysts and light-harvesting material absorbs for water splitting and high-performance optoelectronic devices, respectively. Therefore, in order to make effective use of the visible light in the solar spectrum, it is necessary to discover new efficient approach to overcome the above mentioned problems and broaden the applications of 2D layered SnS<sub>2</sub> and SnSe<sub>2</sub> in water splitting and environmental pollutants degradation fields.

Recently, it has been reported that the visible light response range of some 2D materials can be enhanced by element doping method,<sup>30–33</sup> but it also has some side effects, because the conventional doping with elemental impurities methods usually can introduce any bulk defects into the semiconductor lattice. For instance, An *et al.*<sup>32</sup> have observed that the visible-light photocatalytic activity of Cu-doped SnS<sub>2</sub> nanosheets is much higher than that of pure SnS<sub>2</sub> nanosheets. Moreover, Fe doped SnS<sub>2</sub> nanosheets exhibit excellent visible light absorption behaviour, and the optical absorption coefficient in the visible region increases monotonically with the increase of Fe doping concentration.<sup>33</sup> However, these substitutional doping creates the vacancies and defects in SnS<sub>2</sub> nanosheets, which limits the quantum efficiency and electrochemical performance.<sup>31</sup>

In contrast, the surface charge transfer doping (SCTD) approach is nondestructive and does not induce any bulk defects into the semiconductor lattice.<sup>34,35</sup> And SCTD has been applied to tune both the electronic and optical properties of low dimensional materials,<sup>36–42</sup> which is of fundamental importance to broaden their applications in water splitting and environmental pollutants degradation fields. For example, surface-doped diamond with MoO<sub>3</sub> yielded the concentration of record sheet hole ( $2 \times 10^{14}$  cm<sup>-2</sup>) and launched the quest for its implementation in microelectronic devices, which proposed and demonstrated a general strategy of developing an atomic layer deposition of a hydrogenated MoO<sub>3</sub> layer as a novel efficient surface charge acceptor for transistors.<sup>36</sup> Xia *et al.*<sup>37</sup> also demonstrated a simple yet efficient way to achieve controlled p-type doping on II–VI nanostructures *via* SCTD using MoO<sub>3</sub> as p-type surface dopant, which offers the possibility to create a variety of electronic and optoelectronic devices based on II–VI nanostructures. In addition, Xiong *et al.*<sup>38</sup> demonstrated that K-doped g-C<sub>3</sub>N<sub>4</sub> with a unique electronic structure possessed highly enhanced visible-light photocatalytic performance for NO removal, which could provide new insights into the effects of alkali metal doping on g-C<sub>3</sub>N<sub>4</sub> as well as the design of intercalated photocatalysts with highly efficient visible-light-

driven activity for air purification. Wang *et al.*<sup>39</sup> uncovered a simple hydrothermal recalcination method to prepare a novel potassium (K)-doped porous ultrathin g-C<sub>3</sub>N<sub>4</sub> photocatalyst with efficient catalytic performance, eco-friendly characteristics, and excellent stability. All these studies show that MoO<sub>3</sub> and K are the effective surface dopants to tune the electronic and optical properties of low dimensional materials.

Herein, to enhance the visible light absorption of SnS<sub>2</sub> and SnSe<sub>2</sub>, we performed a systematical investigation on tuning the electronic and optical properties of monolayer SnS<sub>2</sub> and SnSe<sub>2</sub> *via* SCTD with the adsorption of molybdenum trioxide (MoO<sub>3</sub>) and potassium (K) as surface dopants based on the density functional theory (DFT). Our calculations revealed that MoO<sub>3</sub> could act as a strong acceptor to draw electrons from monolayer SnS<sub>2</sub> and SnSe<sub>2</sub>, while K could act as a strong donor to donate electrons to monolayer SnS<sub>2</sub> and SnSe<sub>2</sub>, leading to electron-deficiency and electron-rich surface layers, respectively. With MoO<sub>3</sub> doping, the Fermi level downshifted into valence band region, along with the increase of work function. On the contrary, the absorption of K atom on the monolayer surface upshifted Fermi level into the conduction band region, thus decreasing the work function. On the other hand, the bandgaps of monolayer SnS<sub>2</sub> and SnSe<sub>2</sub> decrease after the MoO<sub>3</sub> and K surface modifications. As a result, new absorption peaks appeared at ~650/~600 nm for monolayer SnS<sub>2</sub>/SnSe<sub>2</sub> after MoO<sub>3</sub> adsorption, while K adsorption led to the appearance of new absorption peaks at ~480/~680 nm for monolayer SnS<sub>2</sub>/SnSe<sub>2</sub>. This work paves the way toward reliable and efficient p- and n-type doping on monolayer SnS<sub>2</sub> and SnSe<sub>2</sub>, thus broaden the applications of 2D layered SnS<sub>2</sub> and SnSe<sub>2</sub> in water splitting and environmental pollutants degradation fields.

## Computational methods

All calculations based on the density functional theory (DFT)<sup>43,44</sup> were carried out by the Cambridge Sequential Total Energy Package (CASTEP) program<sup>45</sup> in Materials Studio 6.1 package of Accelrys Ltd. It is well-known that the Generalized Gradient Approximation (GGA) is more accurate than the Local Density Approximation (LDA) in predicting total energies and structural energy differences.<sup>46–52</sup> Therefore, the GGA with the Perdew–Burke–Ernzerhof functional (PBE)<sup>51,52</sup> was adopted for all geometric optimizations and the electronic structures are performed with the GGA/PBE. Meanwhile, the DFT-D2 method of Grimme<sup>53</sup> was employed to describe the van der Waals interactions in our calculated systems, which is important to correctly describe the interactions between the monolayers and the absorbed molecules. The interactions between valence electrons and ionic core are described by Vanderbilt Ultrasoft Pseudopotential.<sup>54</sup> The energy cutoff is set as 550 eV, and  $6 \times 6 \times 1$  *k*-points with the Monkhorst–Pack<sup>55</sup> scheme in the first Brillouin zone is employed in the present work. Both the adopted cutoff energy and *k*-mesh were tested to be converged in total energy. The vacuum distance normal to the plane is larger than 15 Å to eliminate the image interactions. All structures were fully relaxed, and the convergence criteria for geometry optimization and energy calculation are set as  $2.0 \times$



$10^{-5}$  eV per atom,  $0.02 \text{ eV \AA}^{-1}$ ,  $0.005 \text{ \AA}$  and  $2.0 \times 10^{-6}$  eV per atom for the tolerance of energy, maximum force, maximum ionic displacement and self-consistent field (SCF), respectively. The adsorption energy ( $\Delta E$ ) of a molecular adsorbed on the substrate (monolayers) is defined as:

$$\Delta E = E_{\text{dopant/SnX}_2(\text{X=S, Se})} - E_{\text{SnX}_2(\text{X=S, Se})} - E_{\text{dopant}}$$

where  $E_{\text{dopant/SnX}_2(\text{X=S, Se})}$ ,  $E_{\text{SnX}_2(\text{X=S, Se})}$ , and  $E_{\text{dopant}}$  are the total energy of the surface modified system, intrinsic monolayer  $\text{SnX}_2$  ( $\text{X} = \text{S, Se}$ ), and isolated dopant, respectively.

## Results and discussion

The optimized energy-lowest structures of the  $\text{SnS}_2$  and  $\text{SnSe}_2$  monolayers are presented in Fig. 1a and c, respectively. As a benchmark, we first investigated the structural and electronic properties of pristine monolayer  $\text{SnS}_2$  and  $\text{SnSe}_2$ . The optimized lattice constants of monolayer  $\text{SnS}_2$  and  $\text{SnSe}_2$  from GGA-PBE are  $a = b = 3.71$  and  $3.85 \text{ \AA}$ , respectively, and the bond lengths of Sn–S and Sn–Se are uniformly  $2.58 \text{ \AA}$  and  $2.68 \text{ \AA}$ , which are very close to those of experimental and computational results.<sup>56–60</sup> Although Sn/S or Sn/Se atom has a formal charge of +4/–2 in the neutral state, the effective atomic charge was computed to be +1.52/–0.76 and +1.26/–0.63 for monolayer  $\text{SnS}_2$  and  $\text{SnSe}_2$ , respectively, according to the Mulliken charge population analysis, indicating that the bond between Sn and S/Se is a mixture of covalent and ionic ones.

The analysis of phonon dispersion can provide a reliable test for the quality of structure optimization and the dynamical stability of structures. To check the dynamical stability of the  $\text{SnS}_2$  and  $\text{SnSe}_2$  monolayers as well as whether their structures are well optimized, the phonon spectra were calculated based on the same DFT level and shown in Fig. 1b and d. It is noted that there is no imaginary frequency in both the  $\text{SnS}_2$  and  $\text{SnSe}_2$  monolayer systems, which confirms their kinetical stability and

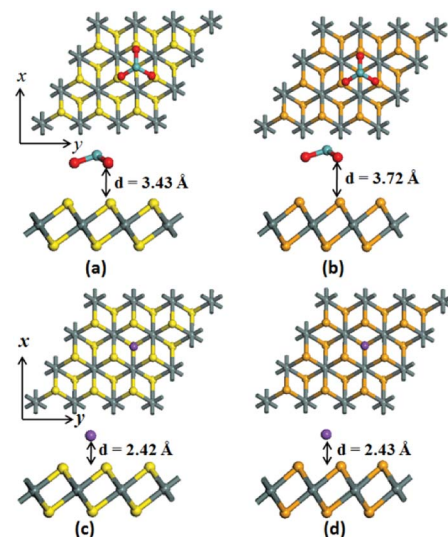


Fig. 2 Top and side views of the optimized lowest-energy configurations for  $\text{MoO}_3$  adsorption on the basal planes of (a)  $\text{SnS}_2$  and (b)  $\text{SnSe}_2$  monolayers, the corresponding (c) and (d) are K modified monolayer  $\text{SnS}_2$  and  $\text{SnSe}_2$ .

well optimized structures. In details, the acoustic and optic vibration frequencies of monolayer  $\text{SnS}_2$  are  $0\text{--}150 \text{ cm}^{-1}$  and  $190\text{--}350 \text{ cm}^{-1}$  (Fig. 1b), while those of the monolayer  $\text{SnSe}_2$  are  $0\text{--}110 \text{ cm}^{-1}$  and  $120\text{--}250 \text{ cm}^{-1}$  (Fig. 1d), respectively. Due to the lighter mass of S atom compared to Se atom, the Debye frequency of  $\text{SnS}_2$  is  $\sim 100 \text{ cm}^{-1}$  bigger than that of monolayer  $\text{SnSe}_2$ . In order to compare the band gaps of bulk phase and monolayers for  $\text{SnS}_2$  and  $\text{SnSe}_2$ , the electronic structures of  $\text{SnS}_2$  and  $\text{SnSe}_2$  were calculated at HSE06 level (shown in Fig. S1†), and the calculated band gaps of bulk phase and monolayers for  $\text{SnS}_2$  and  $\text{SnSe}_2$  are in good accordance with the experimental results,<sup>56,57</sup> showing our calculated results are reliable.

To explore the surface modification effects on the monolayer  $\text{SnS}_2$  and  $\text{SnSe}_2$ , an electron-withdrawing dopant ( $\text{MoO}_3$ ), and an electron-donating dopant (alkali metal atom, K) were chosen in this paper, as shown in Fig. 2. The equilibrium closest vertical distances between  $\text{MoO}_3/\text{K}$  and the monolayer  $\text{SnS}_2/\text{SnSe}_2$  are  $\sim 3.43/2.42$  and  $\sim 3.72/2.43 \text{ \AA}$ , respectively. The equilibrium distances between the K atom and the monolayers are much smaller than that between the  $\text{MoO}_3$  molecule and the monolayers, indicating a much stronger interactions between K atom and the monolayers. This is confirmed by the adsorption energies, where the adsorption energies of K modified monolayers are about two times as those of  $\text{MoO}_3$  modified monolayers (Table 1). The stronger interaction between the K atom and monolayers finally leads to about two times charge transfer amount compared to that of  $\text{MoO}_3$  molecule, as shown in Table 1. Specifically, there are  $0.37$  and  $0.4 |e|$  charges transferred from the  $\text{SnS}_2/\text{SnSe}_2$  monolayers to the  $\text{MoO}_3$  molecule, respectively. As for K atom adsorption,  $0.79$  and  $0.74 |e|$  charges are injected from K atom into the monolayer  $\text{SnS}_2$  and  $\text{SnSe}_2$ , respectively. The large electron withdrawing/donating ability of  $\text{MoO}_3$  and K indicates that they are efficient p- and n-type dopants.

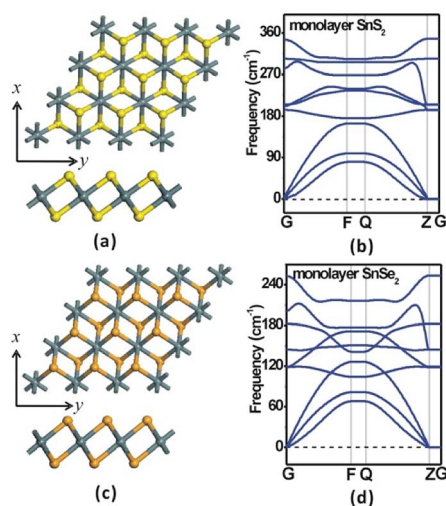


Fig. 1 Top and side views of the optimized monolayer (a)  $\text{SnS}_2$  and (c)  $\text{SnSe}_2$ . (b) and (d) are the phonon spectra of the optimized  $\text{SnS}_2$  and  $\text{SnSe}_2$  monolayers.



**Table 1** Adsorption energy ( $\Delta E$ ), charge transfer ( $q$ ) and change of work function ( $\Delta\Phi$ )<sup>a</sup> of MoO<sub>3</sub> and K modified SnS<sub>2</sub> and SnSe<sub>2</sub> monolayers

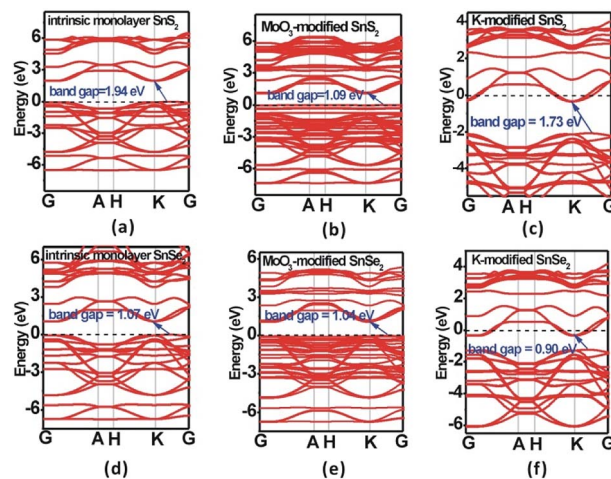
Geometries	$\Delta E/\text{eV}$	$q_{\text{ads}}/e$	$q_{\text{SnX}_2}/e$	$\Delta\Phi/\text{eV}$
MoO <sub>3</sub> -modified SnS <sub>2</sub>	-1.32	-0.37	0.37	0.73
MoO <sub>3</sub> -modified SnSe <sub>2</sub>	-1.44	-0.40	0.40	0.30
K-modified SnS <sub>2</sub>	-3.43	0.79	-0.79	-1.48
K-modified SnSe <sub>2</sub>	-3.22	0.74	-0.74	-1.33

<sup>a</sup>  $\Delta\Phi$  is defined as  $\Delta\Phi = \Phi_{\text{dopant/SnX}_2} - \Phi_{\text{SnX}_2}$ , where  $\Phi_{\text{dopant/SnX}_2}$  and  $\Phi_{\text{SnX}_2}$  are the work functions of the surface modified system and the intrinsic monolayer SnX<sub>2</sub> (X = S, Se), respectively.

The change of carrier concentration will be reflected by the variations of work functions in semiconductors. Therefore, electrostatic potential calculations were further performed to probe the change of work functions ( $\Delta\Phi$ ) for monolayer SnS<sub>2</sub> and SnSe<sub>2</sub> before and after MoO<sub>3</sub> and K doping. As shown in Table 1, the adsorption of MoO<sub>3</sub> molecule on the surface of monolayer SnS<sub>2</sub> and SnSe<sub>2</sub> yields an obvious increase of work function by 0.73 and 0.6 eV, respectively. This result can be attributed to the injection of holes from the MoO<sub>3</sub> molecule into the monolayers, which downshifts the Fermi level of the system. In contrast, a large decrease of work function takes place after the adsorption of K on the monolayer SnS<sub>2</sub> and SnSe<sub>2</sub> due to the upshift of Fermi level into the conduction band region. The above analysis indicates that monolayer SnS<sub>2</sub> and SnSe<sub>2</sub> may be tuned into p-type conductivity by doping with the electron-drawing MoO<sub>3</sub> molecule, while the adsorption of K atoms would enhance the n-type conductivity of monolayer SnS<sub>2</sub> and SnSe<sub>2</sub>.

As mentioned above, both MoO<sub>3</sub> and K can strongly interact with the monolayer SnS<sub>2</sub> and SnSe<sub>2</sub> and a considerable charge transfer between the dopants and monolayers occurs. Such a modification will for sure change the electronic and optical properties of monolayer SnS<sub>2</sub> and SnSe<sub>2</sub>. To illustrate how surface doping changes the electronic properties, the band structures of monolayer SnS<sub>2</sub> and SnSe<sub>2</sub> before and after surface modifications under the same computational conditions were calculated, as shown in Fig. 3.

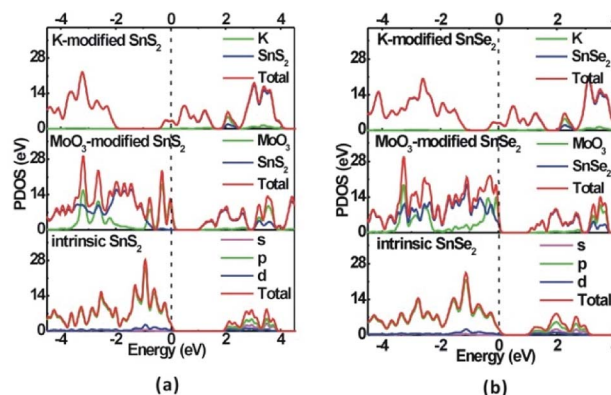
It can be noted that both monolayer SnS<sub>2</sub> and SnSe<sub>2</sub> are indirect-band-gap semiconductors with 1.94 and 1.07 eV bandgaps at the GGA/PBE level (Fig. 3a and d), respectively, but 3.03 and 2.01 eV at the HSE06 level (Fig. S1†), which are in good accordance with experimental and computational results.<sup>56,57</sup> Although the PBE functional usually underestimates bandgaps to some degree, it does not affect our analysis of bandgap variations and Fermi level shifting. Due to the strong non-covalent interaction and considerable charge transfer between the surface dopants (MoO<sub>3</sub> and K) and the monolayer SnS<sub>2</sub> and SnSe<sub>2</sub>, the MoO<sub>3</sub> and K modified systems exhibit decreased bandgaps, as shown in Fig. 3. Interestingly, a new flat energy level is generated in the original bandgaps of MoO<sub>3</sub> modified systems, leading to reduced bandgaps of 1.09 and 1.03 eV, respectively. Moreover, the Fermi level moves to the top of valence band in MoO<sub>3</sub> modified systems, confirming a p-type



**Fig. 3** Band structures of (a) and (d) intrinsic, (b) and (e) MoO<sub>3</sub>-modified, and (c) and (f) K-modified SnS<sub>2</sub> and SnSe<sub>2</sub> monolayers at the GGA-PBE level.

semiconductor characteristic. In contrast, the Fermi level moves into the conduction band after the adsorption of K on the monolayer SnS<sub>2</sub> and SnSe<sub>2</sub>, manifesting the great enhancement of n-type conductivity for monolayer SnS<sub>2</sub> and SnSe<sub>2</sub>. Therefore, it is evident that MoO<sub>3</sub> is a hole dopant and it can be used to achieve p-type doping in monolayer SnS<sub>2</sub> and SnSe<sub>2</sub>, while K as an electron dopant can enhance the n-type conductivity of monolayer SnS<sub>2</sub> and SnSe<sub>2</sub>. The partial density of states (PDOS) of for intrinsic and surface-modified monolayer SnS<sub>2</sub> and SnSe<sub>2</sub> was also computed (Fig. 4), which validates the results from band structure calculations.

To have a deeper insight into the electronic properties of the surface modified monolayer SnS<sub>2</sub> and SnSe<sub>2</sub> systems and visualize the charge transfer between the surface dopants (MoO<sub>3</sub> and K) and the monolayers, we further computed the electron density difference ( $\Delta\rho$ ), which is defined as  $\Delta\rho = \rho_{\text{molecule/substrate}} - \rho_{\text{molecule}} - \rho_{\text{substrate}}$ , in which  $\rho_{\text{molecule/substrate}}$ ,  $\rho_{\text{molecule}}$  and  $\rho_{\text{substrate}}$  denote the electron density of the molecule modified systems, the isolated surface dopants and the monolayers, respectively. The electron density difference illustrates how the electron density changes during the adsorption



**Fig. 4** The partial density of states (PDOS) for intrinsic and surface-modified (a) SnS<sub>2</sub> and (b) SnSe<sub>2</sub> monolayers at the GGA-PBE level.



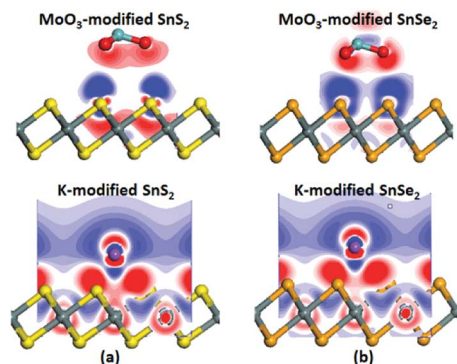


Fig. 5 Electron density difference of MoO<sub>3</sub> and K modified monolayers (a) SnS<sub>2</sub> and (b) SnSe<sub>2</sub>. Red and blue colors represent electron accumulation and depletion, respectively.

process. As shown in Fig. 5, there is a significant variation of the electron density at the interfaces due to the adsorption of MoO<sub>3</sub> and K on the SnS<sub>2</sub>/SnSe<sub>2</sub> monolayers, where the red and blue colors denote the electron loss and enrichment, respectively. A strong electron accumulation is observed around the MoO<sub>3</sub> molecule, while regions of depletion appear on the surface of the SnS<sub>2</sub>/SnSe<sub>2</sub> monolayers. Opposite phenomenon can be found for the K modified systems. These phenomena directly illustrate that the MoO<sub>3</sub> molecule draws electrons from the SnS<sub>2</sub>/SnSe<sub>2</sub> monolayers while the K atoms donate electrons to the SnS<sub>2</sub>/SnSe<sub>2</sub> monolayers. The redistribution of electrons between electron-drawing dopant (MoO<sub>3</sub>) is responsible for the formation of a dipole pointing from the substrate to the MoO<sub>3</sub> molecule, while the redistribution of electrons between electron-donating dopant (K) is responsible for the formation of a dipole pointing from the K atom to the substrate. The above results stemmed from Fig. 5 are supported by the Mulliken population analysis in Table 1. Together with the band structures, it proves the adsorption of MoO<sub>3</sub> and K can dramatically change the electronic properties of SnS<sub>2</sub> and SnSe<sub>2</sub> monolayers.

Since the band structures of the monolayer SnS<sub>2</sub>/SnSe<sub>2</sub> can be effectively tuned by the adsorption of MoO<sub>3</sub> and K, their optical properties, which are directly related to the band structures, are expected to be modified by surface doping as well. Thus, we calculated the imaginary parts of the dielectric functions ( $\epsilon_2$ ), which is an effective parameter to measure the optical absorption ability of materials.<sup>61,62</sup> From Fig. 6, it can be noted that an appreciable new absorption peak appears at  $\sim 650/\sim 600$  nm after MoO<sub>3</sub> adsorbed on the monolayer SnS<sub>2</sub>/SnSe<sub>2</sub>. For K modified monolayer SnS<sub>2</sub>/SnSe<sub>2</sub>, the new adsorption peaks are located at  $\sim 480$  and 680 nm, respectively. The appearance of new absorption peaks is a direct result of the reduced bandgaps with surface doping, which effectively enhances the absorption ability of the monolayer SnS<sub>2</sub>/SnSe<sub>2</sub> in visible region. Interestingly, the adsorption of MoO<sub>3</sub> on monolayer SnS<sub>2</sub>/SnSe<sub>2</sub> not only widens the adsorption region, but also enhances the adsorption intensity, which is particularly useful for light harvesting. The broadened absorption range reveals that the surface doping paves an efficient way to widen the applications of monolayer SnS<sub>2</sub>/SnSe<sub>2</sub> in water splitting and environmental pollutants degradation fields.

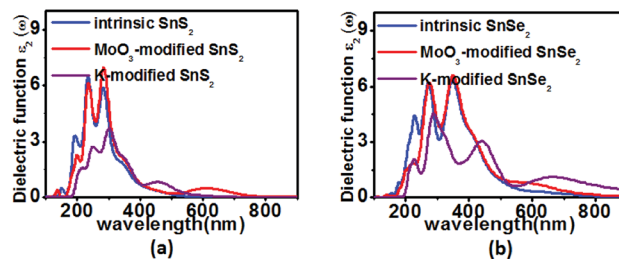


Fig. 6 Computed imaginary dielectric functions versus the wavelength for the pristine (blue lines), MoO<sub>3</sub> (red lines) and K (purple lines) functionalized (a) SnS<sub>2</sub> and (b) SnSe<sub>2</sub> monolayers.

## Conclusions

In conclusion, we systematically investigated the electronic and optical properties of monolayer SnS<sub>2</sub>/SnSe<sub>2</sub> before and after surface modification with electron-drawing (MoO<sub>3</sub>) and electron-donating (K) dopants by means of first principles calculations. It was found that both MoO<sub>3</sub> and K have an obvious effect on the electronic and optical properties of monolayer SnS<sub>2</sub>/SnSe<sub>2</sub>. The adsorption of MoO<sub>3</sub> withdraws the electrons from the monolayer SnS<sub>2</sub> and SnSe<sub>2</sub> and introduces a new flat impurity band in the original band gap of the monolayers, as a result, the Fermi level correspondingly moves to the top of valance band, which leads to a p-type semiconductor characteristic. In contrast, the adsorption of K atom injects electrons into the monolayer SnS<sub>2</sub>/SnSe<sub>2</sub> and the Fermi level moves into the conduction band, which enhances the n-type conductivity of the monolayer SnS<sub>2</sub>/SnSe<sub>2</sub>. The band gaps of both MoO<sub>3</sub> and K doped SnS<sub>2</sub> and SnSe<sub>2</sub> monolayers are reduced due to the significant charge transfer between surface dopants (MoO<sub>3</sub> and K) and monolayers. Moreover, appreciable new absorption peaks appear around  $\sim 650/480$  and  $\sim 600/680$  nm after MoO<sub>3</sub>/K adsorption on the monolayer of SnS<sub>2</sub> and SnSe<sub>2</sub>, respectively, which paves a way to design new efficient sunlight absorber materials. Our results suggest that the surface modification is an efficient way to tune the electronic and optical properties of the monolayer SnS<sub>2</sub>/SnSe<sub>2</sub>, which would broaden the applications of the monolayer SnS<sub>2</sub>/SnSe<sub>2</sub> in water splitting and environmental pollutants degradation fields.

## Conflicts of interest

There are no conflicts to declare.

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